

DHG50X600NA

advanced

 $V_{RRM} = 600V$

 $I_{FAV} = 2x \quad 25A$

 $t_{rr} = 35 \, \text{ns}$

High Performance Fast Recovery Diode Low Loss and Soft Recovery Parallel legs

Sonic Fast Recovery Diode

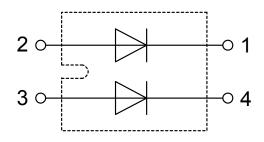
Part number

DHG50X600NA



Backside: Isolated





Features / Advantages:

- Planar passivated chips
- Very low leakage current
 Vary short receiver time
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling





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Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ing voltage	$T_{VJ} = 25^{\circ}C$			600	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			600	V
I _R	reverse current, drain current	V _R = 600 V	$T_{VJ} = 25^{\circ}C$			100	μΑ
		$V_R = 600 V$	$T_{VJ} = 125^{\circ}C$			2	mΑ
V _F	forward voltage drop	I _F = 25 A	$T_{VJ} = 25^{\circ}C$			2.18	V
		I _F = 50 A				2.88	٧
		I _F = 25 A	T _{VJ} = 125°C			2.13	V
		$I_F = 50 \text{ A}$				3.00	V
I _{FAV}	average forward current	T _c = 60°C	T _{vJ} = 150°C			25	Α
		rectangular d = 0.5					i I I I
V _{F0}	threshold voltage		T _{vJ} = 150°C			1.20	V
r _F	slope resistance \(\) for power in	oss calculation only				36	mΩ
R _{thJC}	thermal resistance junction to cas	e				1.2	K/W
R _{thCH}	thermal resistance case to heatsing	nk			0.10		K/W
P _{tot}	total power dissipation		$T_{c} = 25^{\circ}C$			105	W
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			200	Α
CJ	junction capacitance	V _R = 400 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		16		pF
I _{RM}	max. reverse recovery current .	`	$T_{VJ} = 25^{\circ}C$		12		Α
		$I_F = 25 \text{ A}; V_R = 400 \text{ V}$	$T_{VJ} = 125^{\circ}C$		tbd		Α
t _{rr}	reverse recovery time	$-di_F/dt = 600 A/\mu s$	$T_{VJ} = 25^{\circ}C$		35		ns
)	$T_{VJ} = 125$ °C		tbd		ns

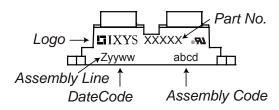




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Package SOT-227B (minibloc)			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					70	Α
T _{stg}	storage temperature				-40		150	°C
T _{VJ}	virtual junction temperatu	ıre			-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
$\mathbf{M}_{\mathbf{T}}$	terminal torque				1.1		1.5	Nm
d _{Spp/App}	creepage distance on surface striking distance through air		terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}			terminal to backside	8.6	6.8			mm
V _{ISOL}	isolation voltage	t = 1 second			3000			V
		t = 1 minute	50/60 Hz, RMS; I _{ISOL} ≤ 1 mA		2500			V

Product Marking



Part number

D = Diode

H = Sonic Fast Recovery Diode

G = extreme fast

50 = Current Rating [A]

X = Parallel legs 600 = Reverse Voltage [V]

NA = SOT-227B (minibloc)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG50X600NA	DHG50X600NA	Tube	10	510221

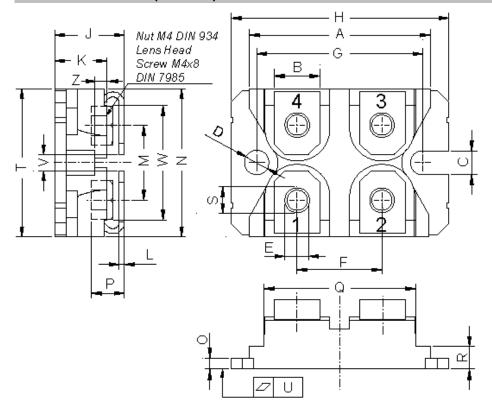
Equivalent Circuits for Simulation			* on die level	T _{VJ} = 150 °C
$I \rightarrow V_0$	R_0	Fast Diode		
V _{0 max}	threshold voltage	1.2		V
$R_{0\text{max}}$	slope resistance *	34		$m\Omega$



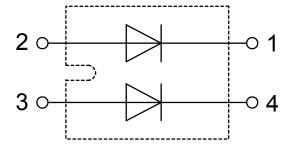


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Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
DIM.	min	max	min	max	
Α	31.50	31.88	1.240	1.255	
В	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
K	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
M	12.50	13.10	0.492	0.516	
N	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Р	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	



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